P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
–60	0.0145 @ V_{GS} = –10 V	–14.4
	0.019 @ V_{GS} = –4.5 V	–12.6

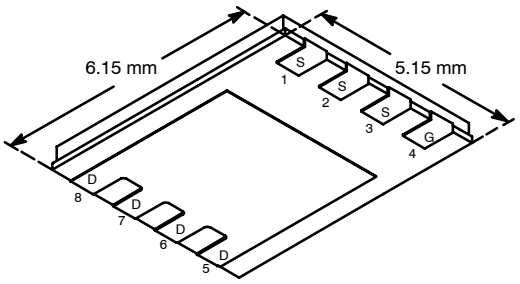
FEATURES

- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK® Package with Low 1.07-mm Profile

APPLICATIONS

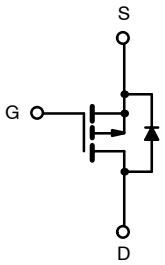
- Automotive
  - 12-V Boardnet
  - High-Side Switches
  - Motor Drives

PowerPAK SO-8



Bottom View

Ordering Information: Si7461DP-T1—E3



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	–60		V
Gate-Source Voltage		V_{GS}	±20		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	–14.4	–8.6	A
	T_A = 70°C		–11.5	–6.9	
Pulsed Drain Current		I_{DM}	–60		
Continuous Source Current (Diode Conduction)[a]		I_S	–4.5	–1.6	
Avalanche Current	L= 0.1 mH	I_{AS}	50		
Single Pulse Avalanche Energy		E_{AS}	125		mJ
Maximum Power Dissipation[a]	T_A = 25°C	P_D	5.4	1.9	W
	T_A = 70°C		3.4	1.2	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	18	23	°C/W
	Steady State		52	65	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.3	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

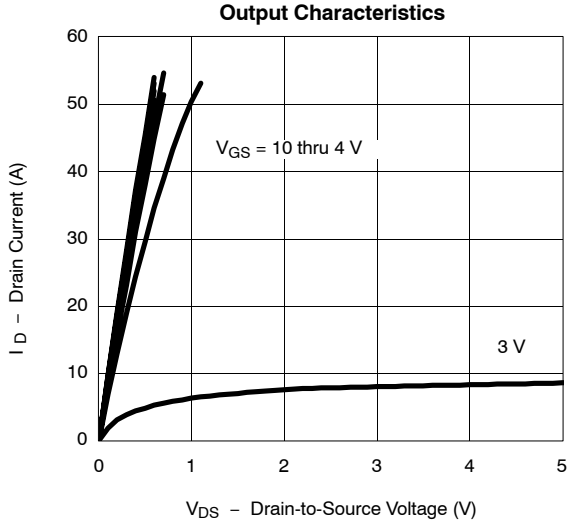
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = −250 μA	−1		−3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = −60 V, V_{GS} = 0 V			−1	μA
		V_{DS} = −60 V, V_{GS} = 0 V, T_J = 70°C			−10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≤ −5 V, V_{GS} = −10 V	−40			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = −10 V, I_D = −14.4 A		0.0115	0.0145	Ω
		V_{GS} = −4.5 V, I_D = −12.6 A		0.015	0.019	
Forward Transconductance[a]	g_{fs}	V_{DS} = −15 V, I_D = −14.4 A		31		S
Diode Forward Voltage[a]	V_{SD}	I_S = −4.5 A, V_{GS} = 0 V		−0.8	−1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = −30 V, V_{GS} = −10 V, I_D = −14.4 A		121	190	nC
Gate-Source Charge	Q_{gs}			20		
Gate-Drain Charge	Q_{gd}			32		
Gate-Resistance	R_g			3		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = −30 V, R_L = 30 Ω I_D ≅ −1 A, V_{GEN} = −10 V, R_g = 6 Ω		20	30	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			205	310	
Fall Time	t_f			90	135	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = −4.5 A, di/dt = 100 A/μs		45	70	

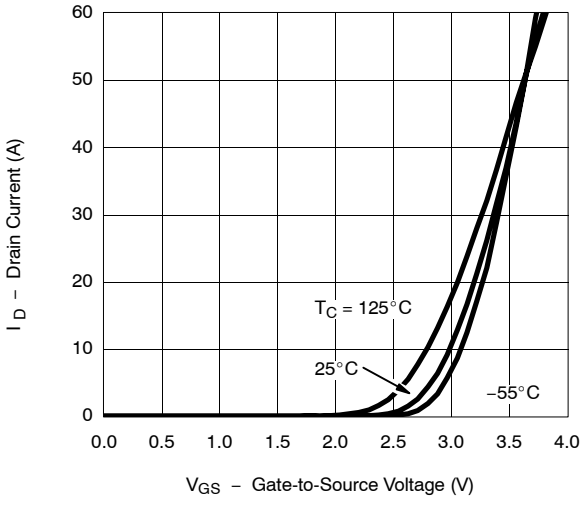
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Output Characteristics

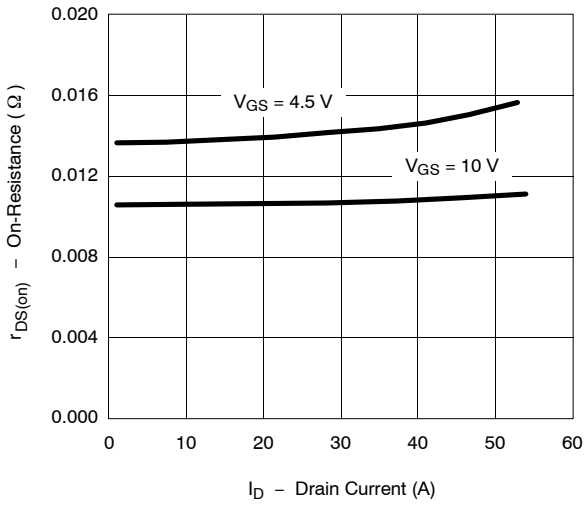


Transfer Characteristics

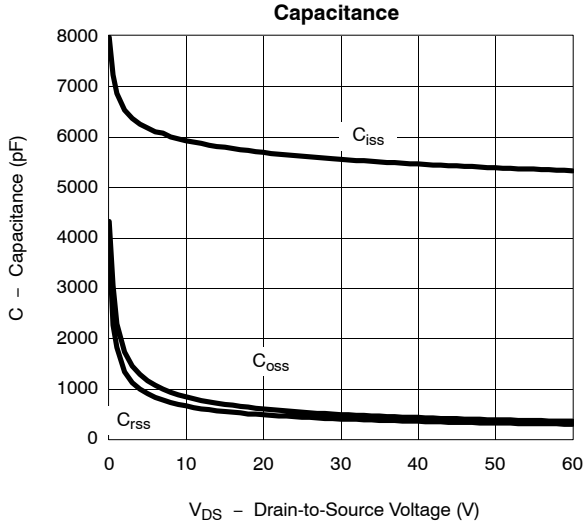


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

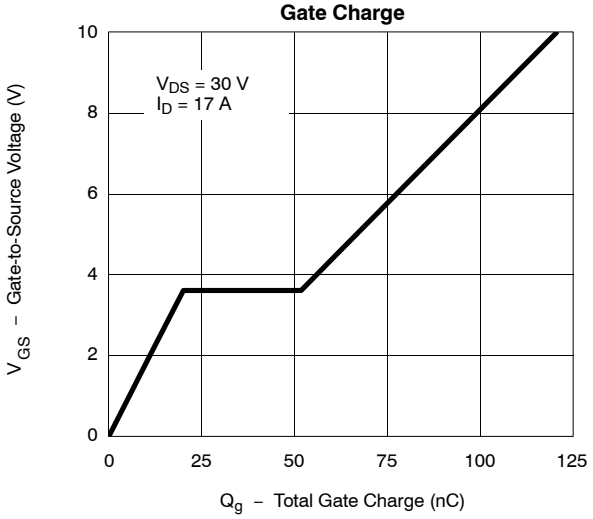
On-Resistance vs. Drain Current



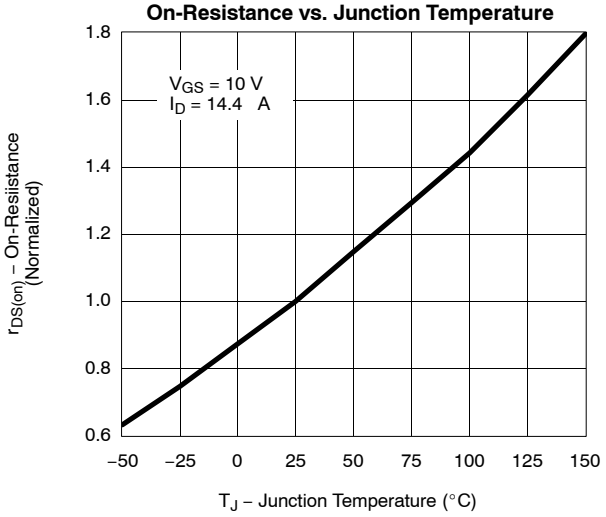
Capacitance



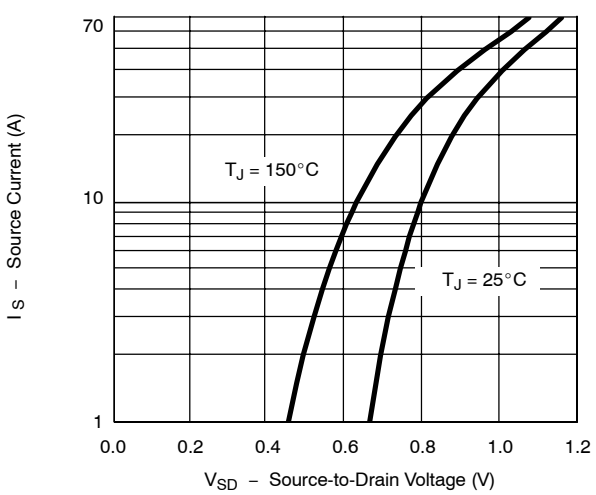
Gate Charge



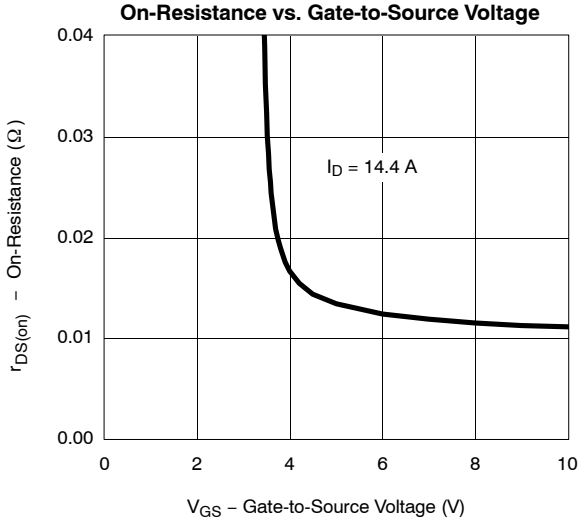
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

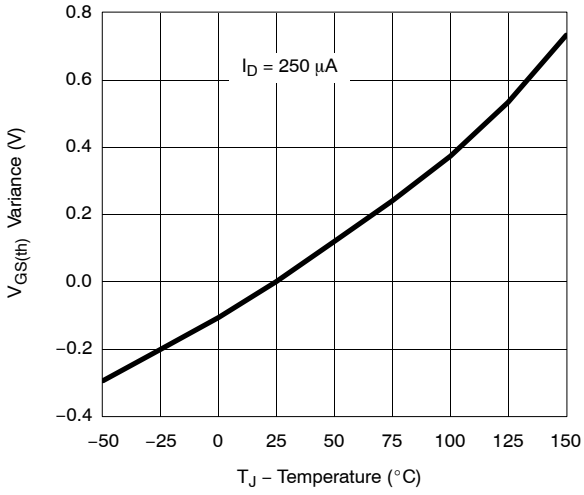


On-Resistance vs. Gate-to-Source Voltage

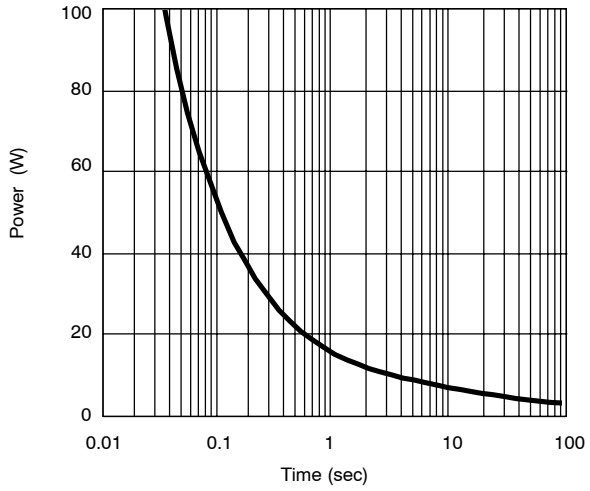


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

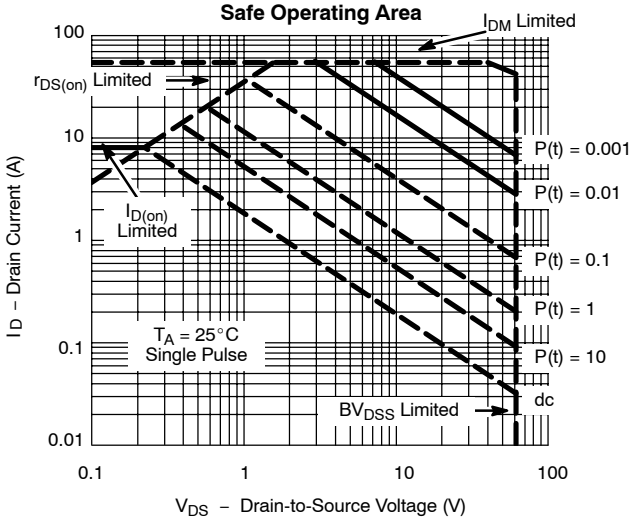
Threshold Voltage



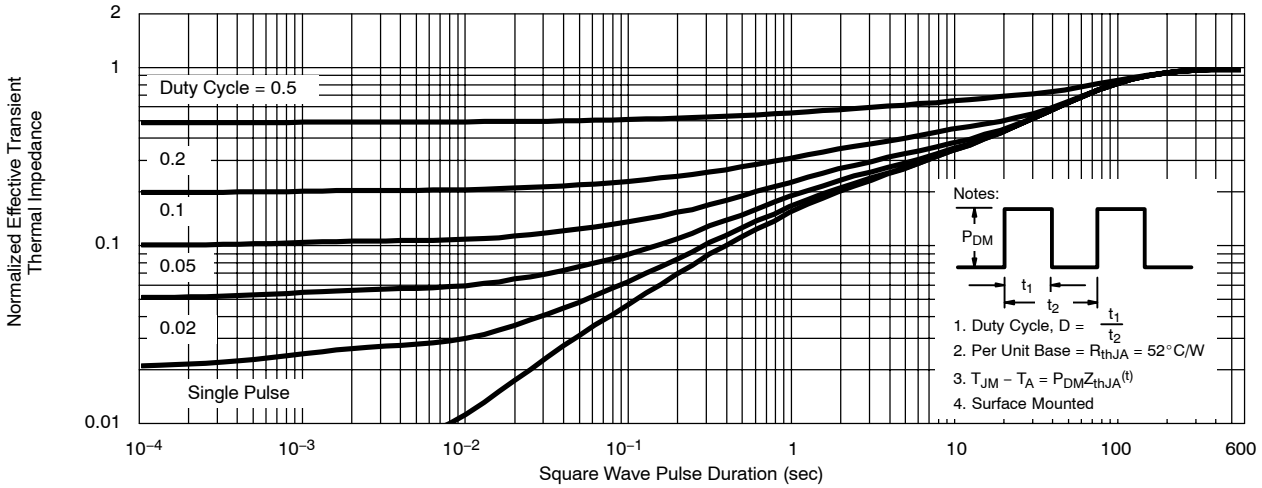
Single Pulse Power, Juncion-To-Ambient



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)